Shoou-Jinn Chang

List of Publications by Year
in descending order

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284	6,141	87888 38	110387 64
papers	citations	h-index	g-index

284	284	284	6034
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Laterally grown ZnO nanowire ethanol gas sensors. Sensors and Actuators B: Chemical, 2007, 126, 473-477.	7.8	298
2	Highly sensitive ZnO nanowire ethanol sensor with Pd adsorption. Applied Physics Letters, 2007, 91, .	3.3	199
3	Highly sensitive ZnO nanowire CO sensors with the adsorption of Au nanoparticles. Nanotechnology, 2008, 19, 175502.	2.6	194
4	Doped ZnO 1D Nanostructures: Synthesis, Properties, and Photodetector Application. Small, 2014, 10, 4562-4585.	10.0	166
5	A New Tri-Band Bandpass Filter Based on Stub-Loaded Step-Impedance Resonator. IEEE Microwave and Wireless Components Letters, 2012, 22, 179-181.	3.2	119
6	A ZnO nanowire-based humidity sensor. Superlattices and Microstructures, 2010, 47, 772-778.	3.1	118
7	Ultraviolet photodetectors with low temperature synthesized vertical ZnO nanowires. Chemical Physics Letters, 2005, 416, 75-78.	2.6	115
8	Cu2O/n-ZnO nanowire solar cells on ZnO:Ga/glass templates. Scripta Materialia, 2007, 57, 53-56.	5.2	114
9	Terahertz multichanneled filter in a superconducting photonic crystal. Optics Express, 2010, 18, 27155.	3.4	113
10	Ultraviolet photodetectors with ZnO nanowires prepared on ZnO:Ga/glass templates. Applied Physics Letters, 2006, 89, 153101.	3.3	101
11	InGaN-AlInGaN multiquantum-well LEDs. IEEE Photonics Technology Letters, 2001, 13, 559-561.	2.5	100
12	Highly Sensitive ZnO Nanowire Acetone Vapor Sensor With Au Adsorption. IEEE Nanotechnology Magazine, 2008, 7, 754-759.	2.0	95
13	High Sensitivity of NO Gas Sensors Based on Novel Ag-Doped ZnO Nanoflowers Enhanced with a UV Light-Emitting Diode. ACS Omega, 2018, 3, 13798-13807.	3.5	92
14	n-UV+Blue/Green/Red White Light Emitting Diode Lamps. Japanese Journal of Applied Physics, 2003, 42, 2284-2287.	1.5	90
15	Novel fabrication of UV photodetector based on ZnO nanowire/p-GaN heterojunction. Chemical Physics Letters, 2009, 476, 69-72.	2.6	88
16	ZnO nanowire-based CO sensors prepared on patterned ZnO:Ga/SiO2/Si templates. Sensors and Actuators B: Chemical, 2007, 125, 498-503.	7.8	85
17	Preparation of Sr2SiO4:Eu3+ phosphors by microwave-assisted sintering and their luminescent properties. Ceramics International, 2012, 38, 125-130.	4.8	74
18	Terahertz temperature-dependent defect mode in a semiconductor-dielectric photonic crystal. Journal of Applied Physics, 2011, 110, .	2.5	72

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19	High detectivity InGaN-GaN multiquantum well p-n junction photodiodes. IEEE Journal of Quantum Electronics, 2003, 39, 681-685.	1.9	67
20	ZnO Branched Nanowires and the p-CuO/n-ZnO Heterojunction Nanostructured Photodetector. IEEE Nanotechnology Magazine, 2013, 12, 263-269.	2.0	62
21	ZnO Nanowire-Based Oxygen Gas Sensor. IEEE Sensors Journal, 2009, 9, 485-489.	4.7	58
22	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. ACS Applied Materials & Interfaces, 2017, 9, 14935-14944.	8.0	57
23	Fabrication of a White-Light-Emitting Diode by Doping Gallium into ZnO Nanowire on a p-GaN Substrate. Journal of Physical Chemistry C, 2010, 114, 12422-12426.	3.1	54
24	A Tri-Band Bandpass Filter With Wide Stopband Using Asymmetric Stub-Loaded Resonators. IEEE Microwave and Wireless Components Letters, 2015, 25, 19-21.	3.2	53
25	Buffer-Facilitated Epitaxial Growth of ZnO Nanowire. Crystal Growth and Design, 2005, 5, 579-583.	3.0	52
26	Vertically well aligned P-doped ZnO nanowires synthesized on ZnOâ€“Ga/glass templates. Chemical Communications, 2005, , 3571.	4.1	51
27	A Novel Method for the Formation of Ladder-like ZnO Nanowires. Crystal Growth and Design, 2006, 6, 1282-1284.	3.0	49
28	GaN-Based Light-Emitting Diode With Sputtered AlN Nucleation Layer. IEEE Photonics Technology Letters, 2012, 24, 294-296.	2.5	49
29	Vertical Single-Crystal ZnO Nanowires Grown on ZnOâ€‰:â€‰Ga/Glass Templates. IEEE Nanotechnology Magazine, 2005, 4, 649-654.	2.0	47
30	A ZnO nanowire vacuum pressure sensor. Nanotechnology, 2008, 19, 095505.	2.6	47
31	Electrical and Optical Characteristics of UV Photodetector With Interlaced ZnO Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 990-995.	2.9	45
32	Well-Aligned, Vertically Al-Doped ZnO Nanowires Synthesized on ZnO:Gaâˆ•Glass Templates. Journal of the Electrochemical Society, 2005, 152, G378.	2.9	44
33	CuO Nanowire-Based Humidity Sensor. IEEE Sensors Journal, 2012, 12, 1884-1888.	4.7	44
34	A Visible-Blind TiO2Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	2.9	41
35	Amorphous Indiumâ€“Galliumâ€“Oxide UV Photodetectors. IEEE Photonics Technology Letters, 2015, 27, 2083-2086.	2.5	41
36	Bandgap-Engineered in Indiumâ€“Galliumâ€“Oxide Ultraviolet Phototransistors. IEEE Photonics Technology Letters, 2015, 27, 915-918.	2.5	41

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37	CO₂Gas Sensors Based on Carbon Nanotube Thin Films Using a Simple Transfer Method on Flexible Substrate. IEEE Sensors Journal, 2015, 15, 7017-7020.	4.7	41
38	Growth of Ga$_{m 2}$O $_{m 3}$ Nanowires and the Fabrication of Solar-Blind Photodetector. IEEE Nanotechnology Magazine, 2011, 10, 1047-1052.	2.0	40
39	${m Ga}_{2}{m O}_{3}$ Nanowire Photodetector Prepared on ${m SiO}_{2}/{m Si}$ Template. IEEE Sensors Journal, 2013, 13, 2368-2373.	4.7	40
40	Field-Emission and Photoelectrical Characteristics of Gaâ€“ZnO Nanorods Photodetector. IEEE Transactions on Electron Devices, 2013, 60, 1905-1910.	3.0	39
41	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	4.7	37
42	Enhanced Extraction and Efficiency of Blue Light-Emitting Diodes Prepared Using Two-Step-Etched Patterned Sapphire Substrates. Journal of the Electrochemical Society, 2009, 156, H874.	2.9	36
43	Carbon Nanotubes With Adsorbed Au for Sensing Gas. IEEE Sensors Journal, 2013, 13, 2423-2427.	4.7	36
44	Transparent gas senor and photodetector based on Al doped ZnO nanowires synthesized on glass substrate. Ceramics International, 2017, 43, 5434-5440.	4.8	36
45	Ultraviolet/Visible Photodetectors Based on pâ€“n NiO/ZnO Nanowires Decorated with Pd Nanoparticles. ACS Applied Nano Materials, 2019, 2, 6343-6351.	5.0	36
46	Transparent ZnO-nanowire-based device for UV light detection and ethanol gas sensing on c-Si solar cell. RSC Advances, 2016, 6, 11146-11150.	3.6	35
47	Enhanced field emission of well-aligned ZnO nanowire arrays illuminated by UV. Chemical Physics Letters, 2010, 490, 176-179.	2.6	34
48	Improved Performance of GaN-Based Blue LEDs With the InGaN Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. IEEE Journal of Quantum Electronics, 2010, 46, 513-517.	1.9	34
49	Improving crystalline morphology and photoluminescent properties of BaY2ZnO5:Eu3+ phosphors prepared using microwave assisted sintering. Materials Letters, 2010, 64, 2548-2550.	2.6	34
50	Bending effects of ZnO nanorod metalâ€“semiconductorâ€“metal photodetectors on flexible polyimide substrate. Nanoscale Research Letters, 2012, 7, 214.	5.7	34
51	Visible-Blind Photodetectors With Mg-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 645-648.	2.5	34
52	Transparent TiN Electrodes in GaN Metalâ€“Semiconductorâ€“Metal Ultraviolet Photodetectors. Japanese Journal of Applied Physics, 2002, 41, 3643-3645.	1.5	32
53	Buckling instabilities in GaN nanotubes under uniaxial compression. Nanotechnology, 2005, 16, 2203-2208.	2.6	31
54	ZnO-Based Ultraviolet Photodetectors With Novel Nanosheet Structures. IEEE Nanotechnology Magazine, 2014, 13, 238-244.	2.0	31

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55	GaN-Based Multiquantum Well Light-Emitting Diodes With Tunnel-Junction-Cascaded Active Regions. IEEE Electron Device Letters, 2015, 36, 366-368.	3.9	31
56	ZnO Nanowire-Based CO Sensors Prepared at Various Temperatures. Journal of the Electrochemical Society, 2007, 154, J393.	2.9	30
57	Ga-Doped ZnO Nanosheet Structure-Based Ultraviolet Photodetector by Low-Temperature Aqueous Solution Method. IEEE Transactions on Electron Devices, 2015, 62, 2924-2927.	3.0	30
58	AlGaN/GaN Metal Oxide Semiconductor Heterostructure Field-Effect Transistor Based on a Liquid Phase Deposited Oxide. Japanese Journal of Applied Physics, 2002, 41, L748-L750.	1.5	29
59	Carbon Nanotube Thin Films Functionalized via Loading of Au Nanoclusters for Flexible Gas Sensors Devices. IEEE Transactions on Electron Devices, 2016, 63, 476-480.	3.0	29
60	Deposition of SiO[sub 2] Layers on GaN by Photochemical Vapor Deposition. Journal of the Electrochemical Society, 2003, 150, C77.	2.9	28
61	Bipolar Ni/ZnO/HfO2/Ni RRAM with multilevel characteristic by different reset bias. Materials Science in Semiconductor Processing, 2015, 35, 30-33.	4.0	28
62	The properties of photo chemical-vapor deposition SiO2 and its application in GaN metal-insulator semiconductor ultraviolet photodetectors. Journal of Electronic Materials, 2003, 32, 395-399.	2.2	27
63	High UV/visible rejection contrast AlGaN/GaN MIS photodetectors. Thin Solid Films, 2006, 498, 133-136.	1.8	27
64	Nonenzymatic Glucose Sensor Based on Au/ZnO Coreâ€“Shell Nanostructures Decorated with Au Nanoparticles and Enhanced with Blue and Green Light. Journal of Physical Chemistry B, 2017, 121, 2931-2941.	2.6	27
65	Fast Detection and Flexible Microfluidic pH Sensors Based on Al-Doped ZnO Nanosheets with a Novel Morphology. ACS Omega, 2019, 4, 19847-19855.	3.5	27
66	A novel method to realize InGaN self-assembled quantum dots by metalorganic chemical vapor deposition. Materials Letters, 2003, 57, 4218-4221.	2.6	26
67	Low-Frequency Noise Characteristics of ZnO Nanorods Schottky Barrier Photodetectors. IEEE Sensors Journal, 2013, 13, 2115-2119.	4.7	26
68	UV Enhanced Field Emission Performance of Mg-Doped ZnO Nanorods. IEEE Transactions on Electron Devices, 2014, 61, 1541-1545.	3.0	26
69	High Density Novel Porous ZnO Nanosheets Based on a Microheater Chip for Ozone Sensors. IEEE Sensors Journal, 2018, 18, 5559-5565.	4.7	26
70	Nitride-Based LEDs With Phosphoric Acid Etched Undercut Sidewalls. IEEE Photonics Technology Letters, 2009, 21, 510-512.	2.5	25
71	Crystalline morphology and photoluminescent properties of YInGe2O7:Eu3+ phosphors prepared from microwave and conventional sintering. Ceramics International, 2011, 37, 749-752.	4.8	25
72	GaN-Based LEDs With a Chirped Multiquantum Barrier Structure. IEEE Photonics Technology Letters, 2012, 24, 1600-1602.	2.5	25

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73	The Effects of Mechanical Uniaxial Stress on Junction Leakage in Nanoscale CMOSFETs. IEEE Transactions on Electron Devices, 2008, 55, 572-577.	3.0	24
74	Simple method to design a tri-band bandpass filter using asymmetric SIRs for GSM, WIMAX, and WLAN applications. Microwave and Optical Technology Letters, 2011, 53, 1573-1576.	1.4	24
75	Effect of Eu3+ concentration on microstructure and photoluminescence of Sr2SiO4:Eu3+ phosphors prepared by microwave assisted sintering. Journal of Luminescence, 2012, 132, 780-783.	3.1	24
76	Low-Frequency Noise Characteristics of In-Doped ZnO Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2043-2046.	2.5	24
77	UV Enhanced Emission Performance of Low Temperature Grown Ga-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 66-69.	2.5	24
78	Highly Stable Ultrathin TiO₂Based Resistive Random Access Memory with Low Operation Voltage. ECS Journal of Solid State Science and Technology, 2018, 7, Q3183-Q3188.	1.8	24
79	Indium-diffused ZnO nanowires synthesized on ITO-buffered Si substrate. Nanotechnology, 2006, 17, 516-519.	2.6	23
80	A lateral ZnO nanowire UV photodetector prepared on a ZnO:Ga/glass template. Semiconductor Science and Technology, 2009, 24, 075005.	2.0	23
81	Deep UV ${m Ta}_{2}{m O}_{5}$/Zinc-Indium-Tin-Oxide Thin Film Photo-Transistor. IEEE Photonics Technology Letters, 2012, 24, 1018-1020.	2.5	23
82	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. Materials, 2017, 10, 126.	2.9	23
83	P-Down InGaN/GaN Multiple Quantum Wells Light-Emitting Diode Structure Grown by Metal-Organic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 2002, 41, 2489-2492.	1.5	22
84	On the Carrier Concentration and Hall Mobility in GaN Epilayers. Japanese Journal of Applied Physics, 2002, 41, L226-L228.	1.5	22
85	Effect of temperature on the deposition of ZnO thin films by successive ionic layer adsorption and reaction. Applied Surface Science, 2012, 258, 8109-8116.	6.1	22
86	Cu-Al interfacial formation and kinetic growth behavior during HTS reliability test. Journal of Materials Processing Technology, 2019, 267, 90-102.	6.3	22
87	High-Indium-Content InGaN/GaN Multiple-Quantum-Well Light-Emitting Diodes. Japanese Journal of Applied Physics, 2003, 42, 2281-2283.	1.5	21
88	ZnO-Nanowire-Based Extended-Gate Field-Effect-Transistor pH Sensors Prepared on Glass Substrate. Science of Advanced Materials, 2012, 4, 1174-1178.	0.7	21
89	Vertical ZnO/ZnGa2O4 coreâ€“shell nanorods grown on ZnO/glass templates by reactive evaporation. Chemical Physics Letters, 2005, 411, 221-224.	2.6	20
90	High hole concentration of p-type InGaN epitaxial layers grown by MOCVD. Thin Solid Films, 2006, 498, 113-117.	1.8	20

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91	Rinsing Effects on Successive Ionic Layer Adsorption and Reaction Method for Deposition of ZnO Thin Films. Journal of the Electrochemical Society, 2011, 158, H208.	2.9	20
92	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. Applied Physics Letters, 2019, 114, .	3.3	20
93	GaN UV photodetector by using transparency antimony-doped tin oxide electrode. Journal of Crystal Growth, 2007, 298, 744-747.	1.5	19
94	Nitride-Based LEDs With High-Reflectance and Wide-Angle Ag Mirror${+}$SiO$_{2}$/TiO$_{2}$ DBR Backside Reflector. Journal of Lightwave Technology, 2011, 29, 1033-1038.	4.6	19
95	Influences of surface reconstruction on the atomic-layer-deposited HfO2/Al2O3/n-InAs metal-oxide-semiconductor capacitors. Applied Physics Letters, 2011, 98, 123509.	3.3	19
96	The Effect of Oxygen Partial Pressure and Annealing Process on the Characteristics of ZnGa₂O₄ÂMSM UV Photodetector. ECS Journal of Solid State Science and Technology, 2019, 8, Q3213-Q3216.	1.8	19
97	Noise Characteristics of ZnO-Nanowire Photodetectors Prepared on ZnO:Ga/Glass Templates. IEEE Sensors Journal, 2007, 7, 1020-1024.	4.7	18
98	Improved Field Emission Properties of Ag-Decorated Multi-Walled Carbon Nanotubes. IEEE Photonics Technology Letters, 2013, 25, 1017-1019.	2.5	18
99	Synthesis of CZTSe nanoink via a facile one-pot heating route based on polyetheramine chelation. Solar Energy Materials and Solar Cells, 2014, 128, 156-165.	6.2	18
100	High Responsivity Mg_xZn_{1â^'x}O Film UV Photodetector Grown by RF Sputtering. IEEE Photonics Technology Letters, 2015, 27, 978-981.	2.5	18
101	Enhanced Field Electron Emission From Zinc-Doped CuO Nanowires. IEEE Electron Device Letters, 2012, 33, 887-889.	3.9	17
102	Different alkali carbonates on the microstructure and photoluminescence properties of BaY2ZnO5:Tb3+ phosphors prepared using the solid-state method. Journal of Physics and Chemistry of Solids, 2013, 74, 344-347.	4.0	17
103	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ${k}$ Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	2.5	17
104	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	2.2	17
105	A New and Simple Means for Self-Assembled Nanostructure:Â Facilitated by Buffer Layer. Journal of Physical Chemistry B, 2004, 108, 18799-18803.	2.6	16
106	Noise Properties of Fe-ZnO Nanorod Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2089-2092.	2.5	16
107	Cascaded GaN Light-Emitting Diodes With Hybrid Tunnel Junction Layers. IEEE Journal of Quantum Electronics, 2015, 51, 1-5.	1.9	16
108	A $hbox{TiO}_{2}$ Nanowire MIS Photodetector With Polymer Insulator. IEEE Electron Device Letters, 2012, 33, 1577-1579.	3.9	15

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109	Enhanced Field Emission Properties of Ga-Doped ZnO Nanosheets by using an Aqueous Solution at Room Temperature. IEEE Transactions on Electron Devices, 2014, 61, 4192-4196.	3.0	15
110	A low-temperature ZnO nanowire ethanol gas sensor prepared on plastic substrate. Materials Research Express, 2016, 3, 095002.	1.6	15
111	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. Nanomaterials, 2017, 7, 156.	4.1	15
112	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. ECS Journal of Solid State Science and Technology, 2019, 8, Q3140-Q3143.	1.8	15
113	Nitride based Power Chip with Indium-Tin-Oxide p-Contact and Al Back-Side Reflector. Japanese Journal of Applied Physics, 2005, 44, 2462-2464.	1.5	14
114	GaN-Based MSM Photodetectors Prepared on Patterned Sapphire Substrates. IEEE Photonics Technology Letters, 2008, 20, 1866-1868.	2.5	14
115	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. IEEE Transactions on Electron Devices, 2013, 60, 1178-1182.	3.0	14
116	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga₂O₃ Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	2.9	14
117	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	2.6	14
118	AlGaInP-sapphire glue bonded light-emitting diodes. IEEE Journal of Quantum Electronics, 2002, 38, 1390-1394.	1.9	13
119	Growth and Characterization of Sparsely Dispersed ZnO Nanowires. Journal of the Electrochemical Society, 2007, 154, H153.	2.9	13
120	GaN-Based LEDs Output Power Improved by Textured GaN/Sapphire Interface Using <emphasis emphasistype="italic">In Situ</emphasis> <formula formulatype="inline"><tex Notation="TeX">$hbox{SiH}_{f 4}$</tex> </formula> Treatment Process During Epitaxial Growth. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1275-1280.	2.9	13
121	A mid-infrared tunable filter in a semiconductorâ€“dielectric photonic crystal containing doped semiconductor defect. Solid State Communications, 2011, 151, 1677-1680.	1.9	13
122	The effects of sintering method on crystalline morphology and photoluminescent properties of BaY2ZnO5:Tb3+. Ceramics International, 2011, 37, 1521-1524.	4.8	13
123	Recovery of thermal-degraded ZnO photodetector by embedding nano silver oxide nanoparticles. Applied Surface Science, 2013, 279, 31-35.	6.1	13
124	Fabrication and sulfurization of Cu2SnS3 thin films with tuning the concentration of Cu-Sn-S precursor ink. Applied Surface Science, 2016, 388, 71-76.	6.1	13
125	Corrosion-induced degradation and its mechanism study of Cuâ€“Al interface for Cu-wire bonding under HAST conditions. Journal of Alloys and Compounds, 2020, 825, 154046.	5.5	13
126	The characteristics of different transparent electrodes on GaN photodetectors. Materials Chemistry and Physics, 2003, 80, 201-204.	4.0	12

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127	InGaN/GaN Multi-Quantum Well Metal-Insulator Semiconductor Photodetectors with Photo-CVD SiO2Layers. Japanese Journal of Applied Physics, 2004, 43, 2008-2010.	1.5	12
128	Selective growth of vertical ZnO nanowires on ZnO:Gaâˆ•Si[sub 3]N[sub 4]âˆ•SiO[sub 2]âˆ•Si templates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2292.	1.6	12
129	Nitride-based LEDs with MQW active regions grown by different temperature profiles. IEEE Photonics Technology Letters, 2005, 17, 1806-1808.	2.5	12
130	High-Brightness InGaNâ€“GaN Power Flip-Chip LEDs. Journal of Lightwave Technology, 2009, 27, 1985-1989.	4.6	12
131	Impact of stress-memorization technique induced-tensile strain on low frequency noise in n-channel metal-oxide-semiconductor transistors. Applied Physics Letters, 2010, 97, 123501.	3.3	12
132	Improvement of n-ZnO/p-Si photodiodes by embedding of silver nanoparticles. Journal of Nanoparticle Research, 2011, 13, 4757-4763.	1.9	12
133	InGaP/GaAs/Ge tripleâ€junction solar cells with ZnO nanowires. Progress in Photovoltaics: Research and Applications, 2013, 21, 1645-1652.	8.1	12
134	UV Enhanced Indium-Doped ZnO Nanorod Field Emitter. IEEE Transactions on Electron Devices, 2013, 60, 3901-3906.	3.0	12
135	Characteristics of tantalum-doped silicon oxide-based resistive random access memory. Materials Science in Semiconductor Processing, 2014, 27, 293-296.	4.0	12
136	UV Enhanced Field Emission Properties of Ga-Doped ZnO Nanosheets. IEEE Transactions on Electron Devices, 2015, 62, 2033-2037.	3.0	12
137	Highly stable ITO/Zn2TiO4/Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	3.6	12
138	AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. Japanese Journal of Applied Physics, 1996, 35, 4199-4202.	1.5	11
139	1.54 Î¼m electroluminescence from erbium-doped SiGe light emitting diodes. Journal of Applied Physics, 1998, 83, 1426-1428.	2.5	11
140	Indiumâ€“Tin-Oxide Metalâ€“Insulatorâ€“Semiconductor GaN Ultraviolet Photodetectors Using Liquid-Phase-Deposition Oxide. Japanese Journal of Applied Physics, 2007, 46, 5119.	1.5	11
141	Magnetooptical Effects in Wave Properties for a Semiconductor Photonic Crystal at Near-Infrared. IEEE Photonics Journal, 2012, 4, 903-911.	2.0	11
142	Microstructure and photoluminescent properties of Sr2SiO4:Eu3+ phosphors with various NH4Cl flux concentrations. Materials Research Bulletin, 2012, 47, 1412-1416.	5.2	11
143	$etahbox{-}{m Ga}_{2}{m O}_{3}$ Nanowires-Based Humidity Sensors Prepared on GaN/Sapphire Substrate. IEEE Sensors Journal, 2013, 13, 4891-4896.	4.7	11
144	Numerical Simulation of GaN-Based LEDs With Chirped Multiquantum Barrier Structure. IEEE Journal of Quantum Electronics, 2013, 49, 436-442.	1.9	11

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145	IMPROVEMENT IN THERMAL DEGRADATION OF ZnO PHOTODETECTOR BY EMBEDDING SILVER OXIDE NANOPARTICLES. Functional Materials Letters, 2013, 06, 1350001.	1.2	11
146	Structural and Raman properties of silver-doped ZnO nanorod arrays using electrically induced crystallization process. Materials Research Bulletin, 2015, 64, 274-278.	5.2	11
147	Electron field emission enhancement of hybrid Cu/CuO nanowires fabricated by rapid thermal reduction of CuO nanowires. RSC Advances, 2015, 5, 54220-54224.	3.6	11
148	Enhancement in the structure quality of ZnO nanorods by diluted Co dopants: Analyses via optical second harmonic generation. Journal of Applied Physics, 2015, 117, .	2.5	11
149	Two-bit-per-cell resistive switching memory device with a Ti/MgZnO/Pt structure. RSC Advances, 2015, 5, 88166-88170.	3.6	11
150	UV Enhanced Field Emission Properties of ZnO Nanosheets With Different NaOH Concentration. IEEE Nanotechnology Magazine, 2015, 14, 776-781.	2.0	11
151	White-Light Emission From GaN-Based TJ LEDs Coated With Red Phosphor. IEEE Electron Device Letters, 2016, 37, 1150-1153.	3.9	11
152	Deposition of SiO[sub 2] layers on 4Hâ€“SiC by photochemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 329.	1.6	10
153	Influence of the Formation of the Second Phase in ZnOâˆ•Ga Nanowire Systems. Journal of the Electrochemical Society, 2006, 153, G333.	2.9	10
154	AlGaInP-Based LEDs With a ${m p}^{+}$-GaP Window Layer and a Thermally Annealed ITO Contact. IEEE Journal of Quantum Electronics, 2011, 47, 803-809.	1.9	10
155	Synthesis of Cu2ZnSnSe4 nanocrystals from metal sources using a facile process in isophorondiamine. Materials Letters, 2013, 98, 71-73.	2.6	10
156	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. ECS Journal of Solid State Science and Technology, 2019, 8, Q3034-Q3040.	1.8	10
157	Electrical derivative characteristics of ion-implanted AlGaInP/GaInP multi-quantum well lasers. Solid-State Electronics, 1998, 42, 1867-1869.	1.4	9
158	Low-frequency noise characteristics of GaN-based UV photodiodes with AlN/GaN buffer layers prepared on Si substrates. Journal of Crystal Growth, 2009, 311, 3003-3006.	1.5	9
159	Characteristics of InGaN-Based Light-Emitting Diodes on Patterned Sapphire Substrates with Various Pattern Heights. Journal of Nanomaterials, 2012, 2012, 1-6.	2.7	9
160	Comparison studies of InGaN epitaxy with trimethylgallium and triethylgallium for photosensors application. Materials Chemistry and Physics, 2012, 134, 899-904.	4.0	9
161	GaN-Based LEDs With Sapphire Debris Removed by Phosphoric Etching. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2012, 2, 349-353.	2.5	9
162	Microstructure and photoluminescent properties of BaY2ZnO5:Tb3+ phosphors with addition of lithium carbonate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 375-379.	3.5	9

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